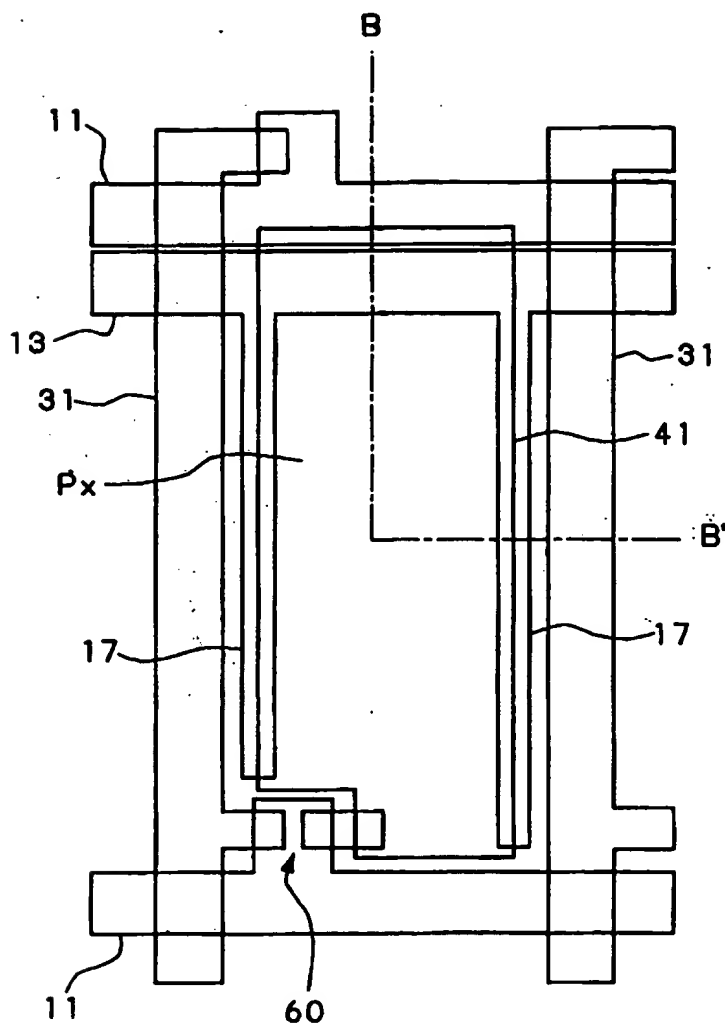
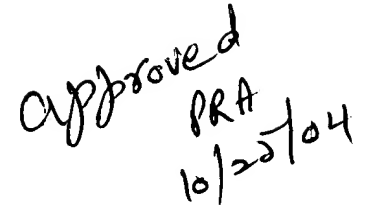




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10/25/04

FIG. 8





A detailed cross-sectional diagram of a semiconductor device. The structure consists of several horizontal layers labeled 1 through 8. Layer 1 is at the bottom, followed by layer 2 which contains rectangular features 11 and 17. Layer 3 has a wavy top surface and contains features 41 and 31. Layer 4 is above layer 3. Layer 5 is a thick central layer containing two horizontal arrows pointing left, labeled 'Or' and 'Lc'. Above layer 5 are layers 6, 7, and 8. Layer 7 contains a feature labeled 14. A bracket on the right side groups layers 6, 7, and 8 as 'Tb'. Another bracket on the right side groups layers 1, 2, and 3 as 'Ab'. An arrow labeled 'Px' points downwards towards the top of the stack.

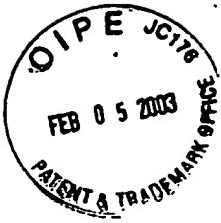
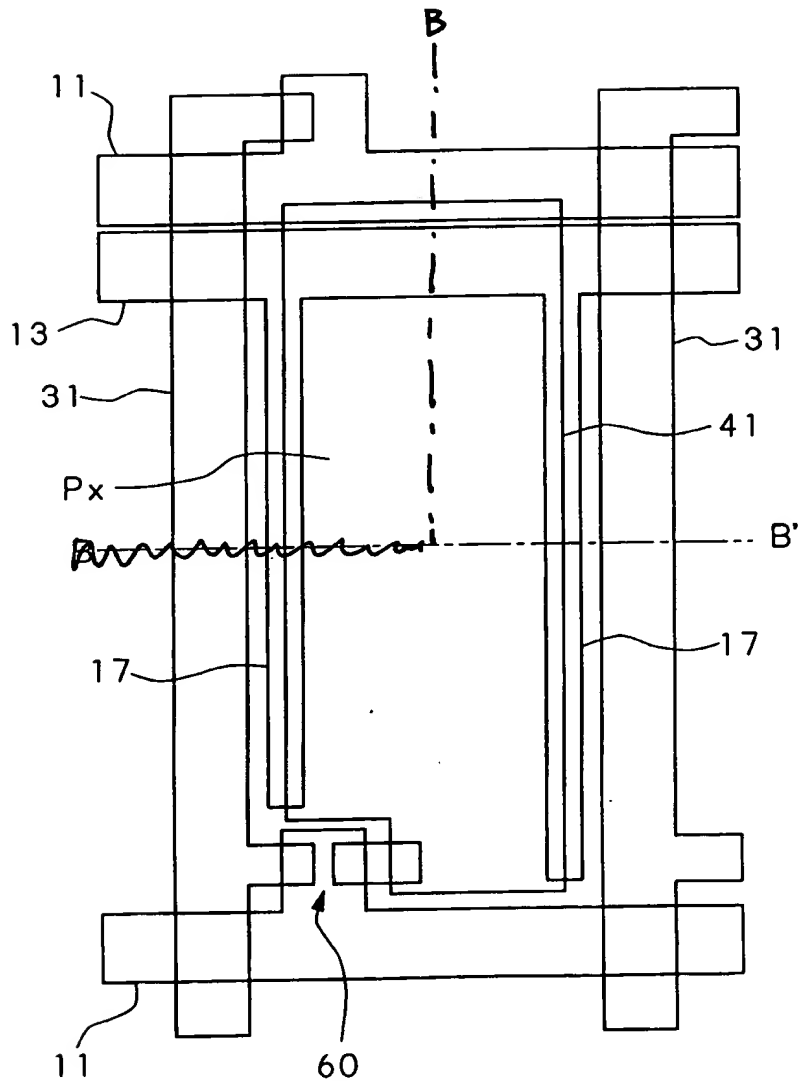
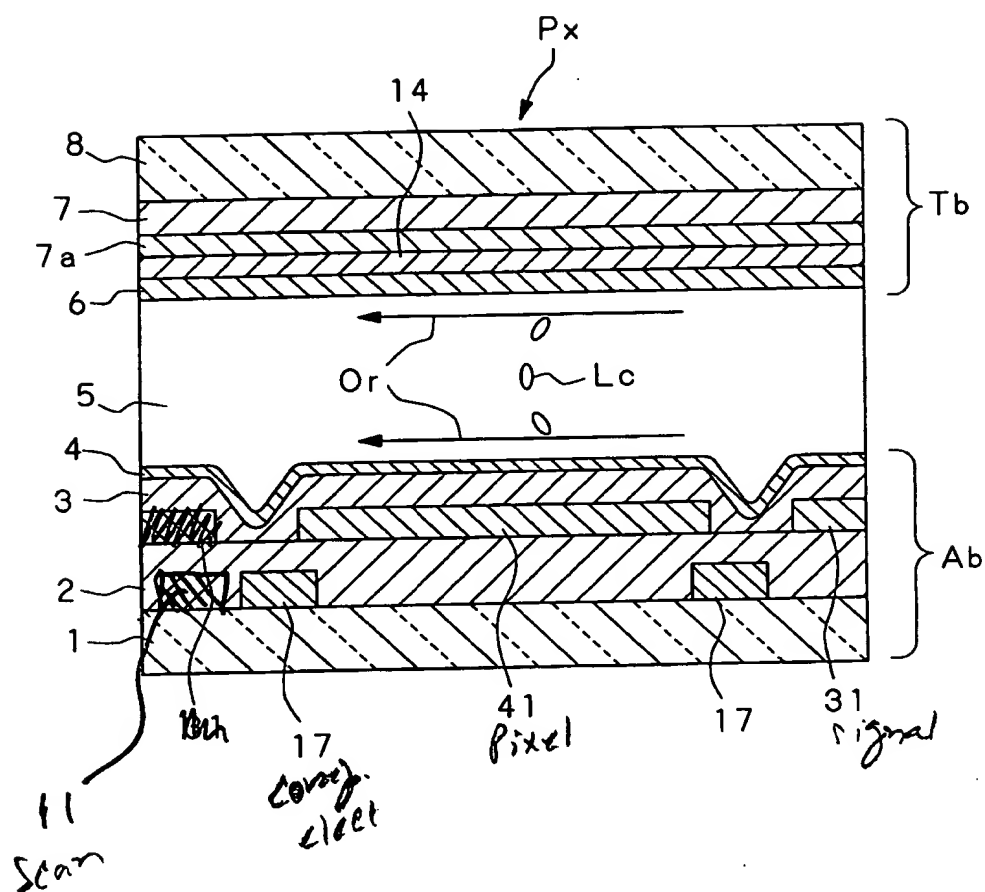


FIG. 8



X

FIG. 9



Figs. 9 & 10
 do not reconcile.